Hang Zang

List of Publications by Year
in descending order

12	253	1040056 9	1199594 12
papers	citations	h-index	g-index

13	13	13	471
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Quantum engineering of non-equilibrium efficient p-doping in ultra-wide band-gap nitrides. Light: Science and Applications, 2021, 10, 69.	16.6	42
2	Quantum Interference in Singlet Fission: J- and H-Aggregate Behavior. Journal of Physical Chemistry Letters, 2017, 8, 5105-5112.	4.6	37
3	Effects of Charge Transfer State and Exciton Migration on Singlet Fission Dynamics in Organic Aggregates. Journal of Physical Chemistry C, 2016, 120, 13351-13359.	3.1	31
4	The formation mechanism of voids in physical vapor deposited AlN epilayer during high temperature annealing. Applied Physics Letters, 2020, 116, .	3.3	28
5	Origination and evolution of point defects in AlN film annealed at high temperature. Journal of Luminescence, 2021, 235, 118032.	3.1	25
6	Generalized timeâ€dependent approaches to vibrationally resolved electronic and Raman spectra: Theory and applications. International Journal of Quantum Chemistry, 2015, 115, 550-563.	2.0	24
7	Improved nucleation of AlN on in situ nitrogen doped graphene for GaN quasi-van der Waals epitaxy. Applied Physics Letters, 2020, 117, .	3.3	22
8	Elimination of the internal electrostatic field in two-dimensional GaN-based semiconductors. Npj 2D Materials and Applications, 2020, 4, .	7.9	16
9	Charge Carrier Mobilities and Singlet Fission Dynamics in Thienoquinoidal Compounds. Journal of Physical Chemistry C, 2017, 121, 22587-22596.	3.1	10
10	Cation Vacancy in Wide Bandgap IIIâ€Nitrides as Singleâ€Photon Emitter: A Firstâ€Principles Investigation. Advanced Science, 2021, 8, e2100100.	11.2	8
11	Point Defects in Monolayer h-AlN as Candidates for Single-Photon Emission. ACS Applied Materials & Interfaces, 2021, 13, 37380-37387.	8.0	7
12	Thickness and strain engineering of structural and electronic properties for 2D square-octagon AlN. International Journal of Smart and Nano Materials, 2020, 11, 288-297.	4.2	1